

MOSFET

650V CoolMOS™ CE Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and Eoss
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

PC Silverbox, Adapters, LCD & PDP TV and indoor Lighting

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

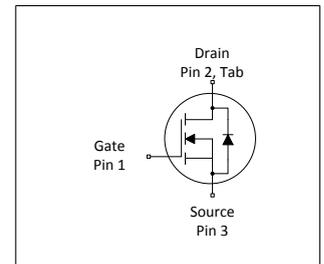


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	1000	$m\Omega$
$I_{d,typ}$	7.2	A
$Q_{g,typ}$	15.3	nC
$I_{D,pulse}$	12	A
$E_{oss}@400V$	1.5	μJ

Type / Ordering Code	Package	Marking	Related Links
IPA65R1K0CE	PG-TO 220 FullPAK	65S1K0CE	see Appendix A

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	7.2 4.6	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	12	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	50	mJ	$I_D=1\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	0.15	mJ	$I_D=1\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, repetitive	I_{AR}	-	-	1.0	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots480\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation (TO220)	P_{tot}	-	-	68	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	5.1	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	12	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di _f /dt	-	-	500	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 8
Mounting torque (FullPAK) TO-220FP	-	-	-	50	Ncm	M2.5 screws
Insulation withstand voltage for TO-220FP	V_{ISO}	-	-	2500	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.50$, TO220 equivalent

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.8	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	80	°C/W	leaded
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	2.5	3.0	3.5	V	$V_{DS}=V_{GS}, I_D=0.2mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=650, V_{GS}=0V, T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.86	1.00	Ω	$V_{GS}=10V, I_D=1.5A, T_j=25^\circ\text{C}$ $V_{GS}=10V, I_D=1.5A, T_j=150^\circ\text{C}$
Gate resistance	R_G	-	5.5	-	Ω	$f=1\text{MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	328	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Output capacitance	C_{oss}	-	23	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	14	-	pF	$V_{GS}=0V, V_{DS}=0\dots480V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	58.5	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0\dots480V$
Turn-on delay time	$t_{d(on)}$	-	6.6	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A,$ $R_G=10.2\Omega$; see table 9
Rise time	t_r	-	5.2	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A,$ $R_G=10.2\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	41	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A,$ $R_G=10.2\Omega$; see table 9
Fall time	t_f	-	13.6	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.2A,$ $R_G=10.2\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	1.8	-	nC	$V_{DD}=480V, I_D=2.2A, V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	8	-	nC	$V_{DD}=480V, I_D=2.2A, V_{GS}=0$ to 10V
Gate charge total	Q_g	-	15.3	-	nC	$V_{DD}=480V, I_D=2.2A, V_{GS}=0$ to 10V
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=480V, I_D=2.2A, V_{GS}=0$ to 10V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{o(BR)DSS}$

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{o(BR)DSS}$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=2.2A, T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	226	-	ns	$V_R=400V, I_F=2.2A, di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	1.3	-	μC	$V_R=400V, I_F=2.2A, di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	9.9	-	A	$V_R=400V, I_F=2.2A, di_F/dt=100A/\mu s$; see table 8

4 Electrical characteristics diagrams

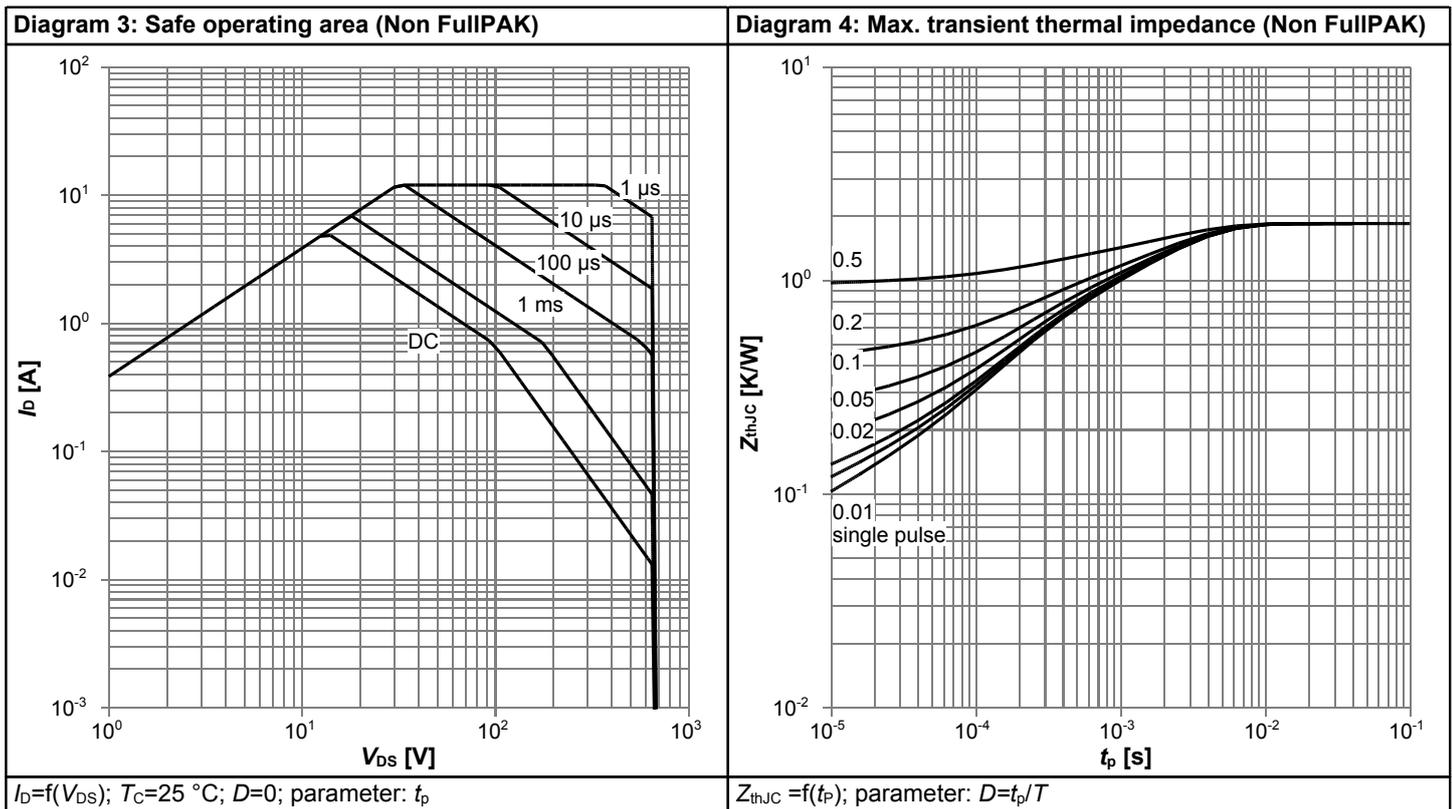
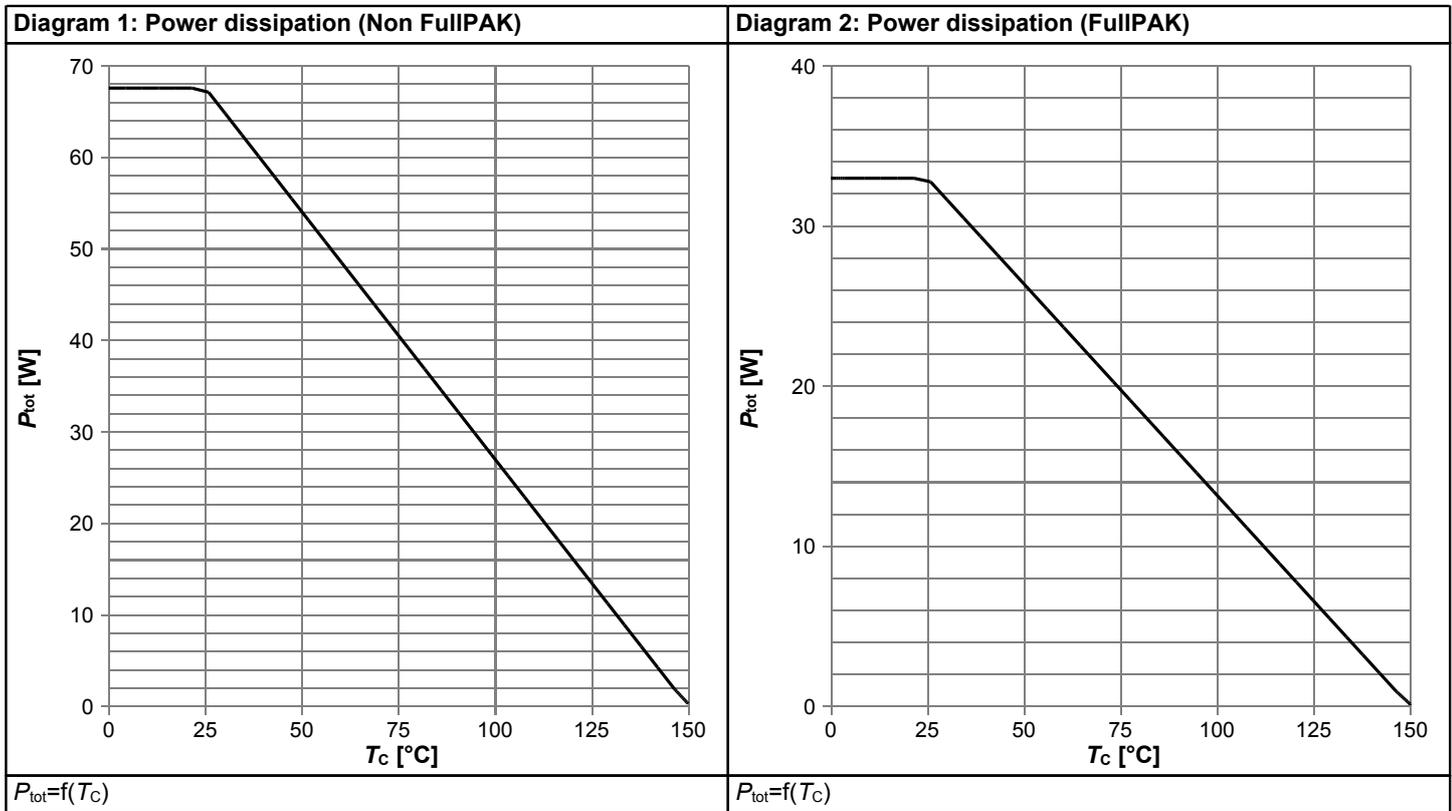
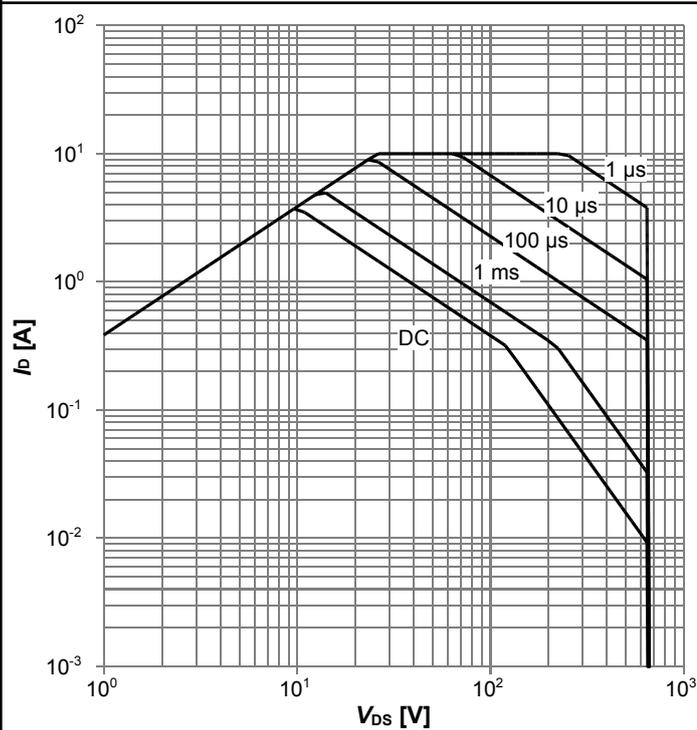
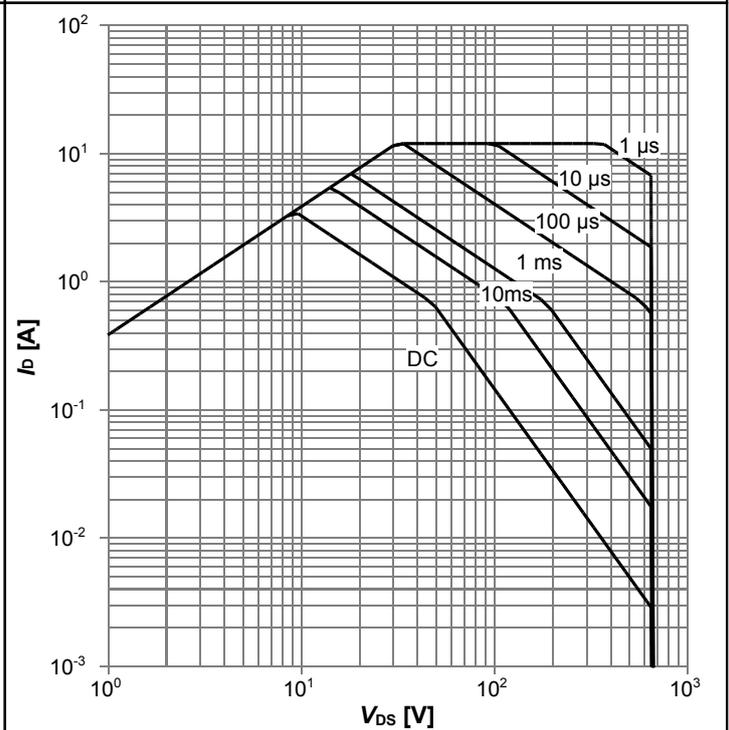


Diagram 5: Safe operating area (Non FullPAK)



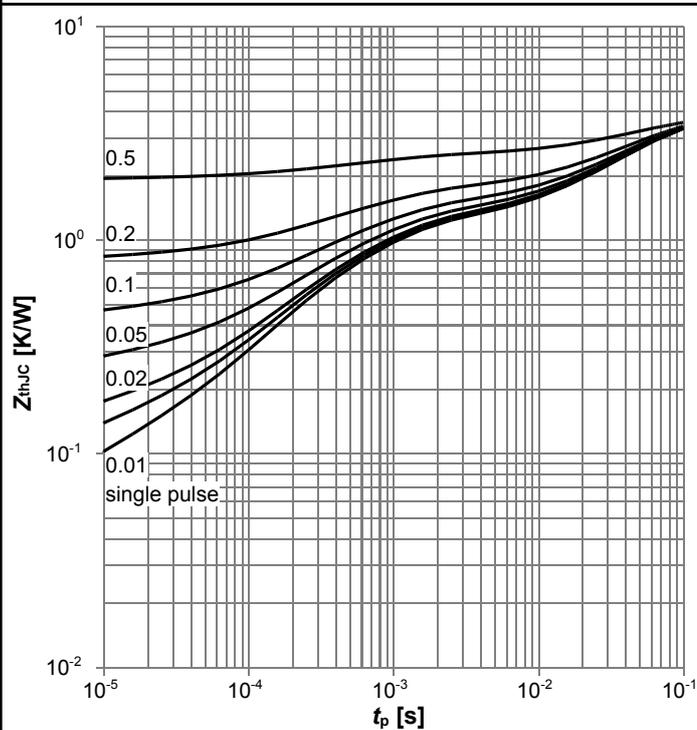
$I_b = f(V_{Ds}); T_C = 80\text{ °C}; D = 0; \text{parameter: } t_p$

Diagram 6: Safe operating area (FullPAK)



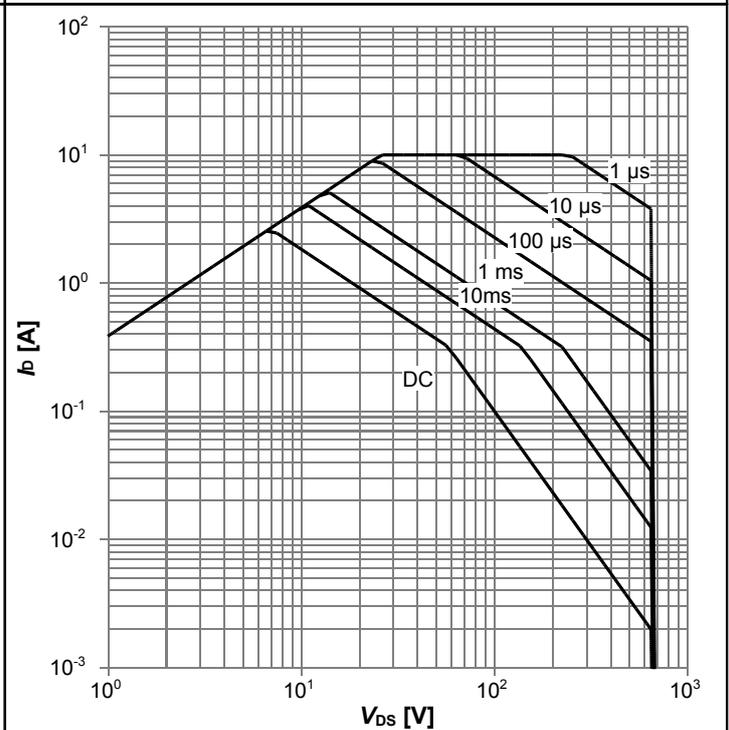
$I_b = f(V_{Ds}); T_C = 25\text{ °C}; D = 0; \text{parameter: } t_p$

Diagram 7: Max. transient thermal impedance (FullPAK)



$Z_{thJC} = f(t_p); \text{parameter: } D = t_p/T$

Diagram 8: Safe operating area (FullPAK)

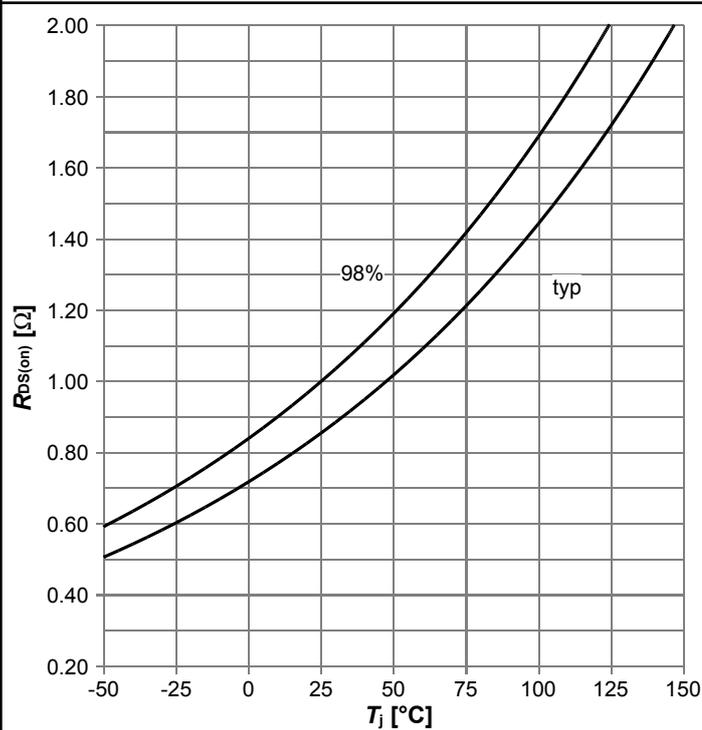


$I_b = f(V_{Ds}); T_C = 80\text{ °C}; D = 0; \text{parameter: } t_p$

650V CoolMOS™ CE Power Transistor

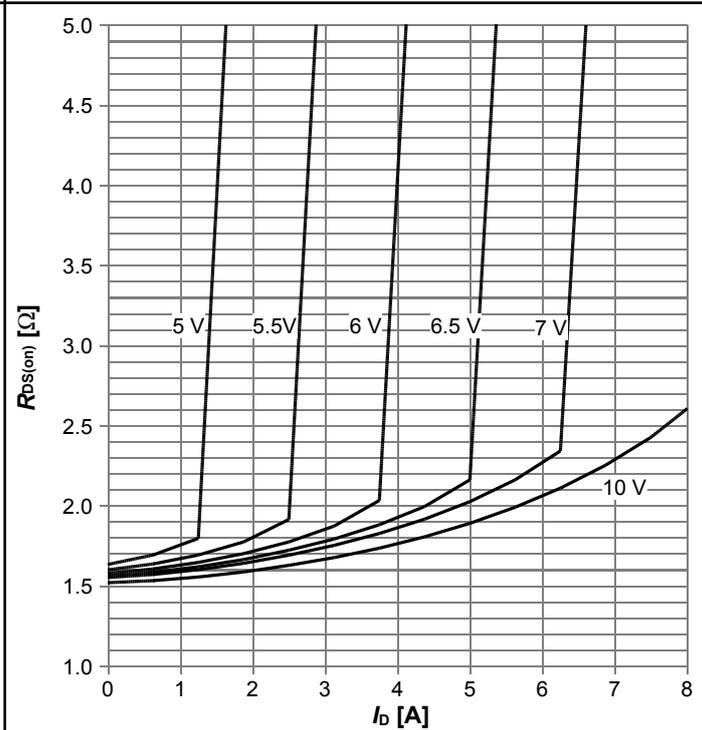
IPA65R1K0CE

Diagram 9: Drain-source on-state resistance



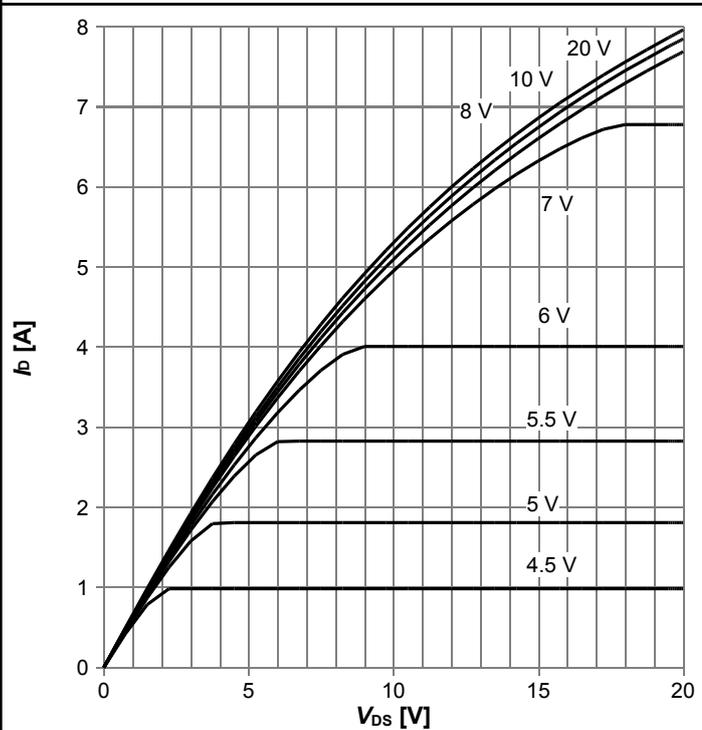
$R_{DS(on)}=f(T_j)$; $I_D=1.5\text{ A}$; $V_{GS}=10\text{ V}$

Diagram 10: Typ. drain-source on-state resistance



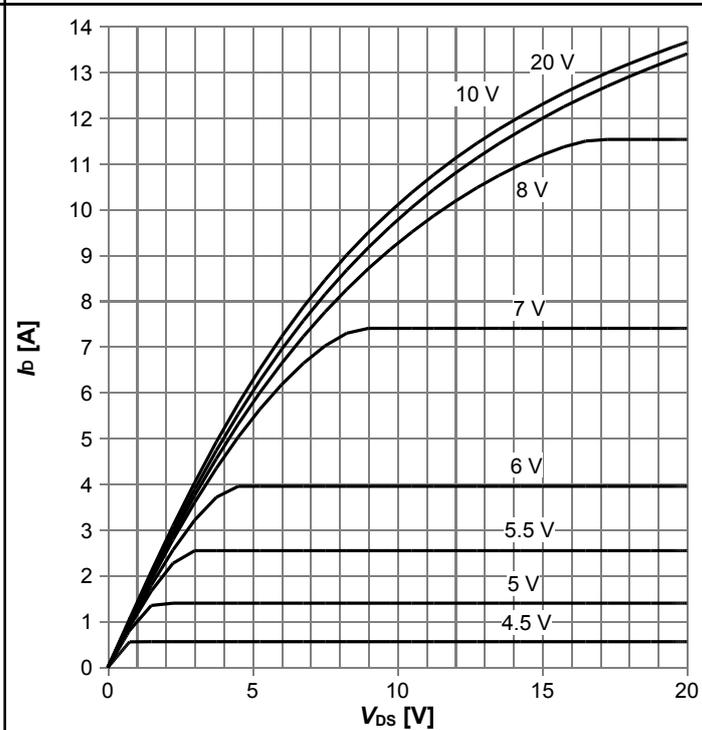
$R_{DS(on)}=f(I_D)$; $T_j=125\text{ }^{\circ}\text{C}$; parameter: V_{GS}

Diagram 11: Typ. output characteristics



$I_D=f(V_{DS})$; $T_j=125\text{ }^{\circ}\text{C}$; parameter: V_{GS}

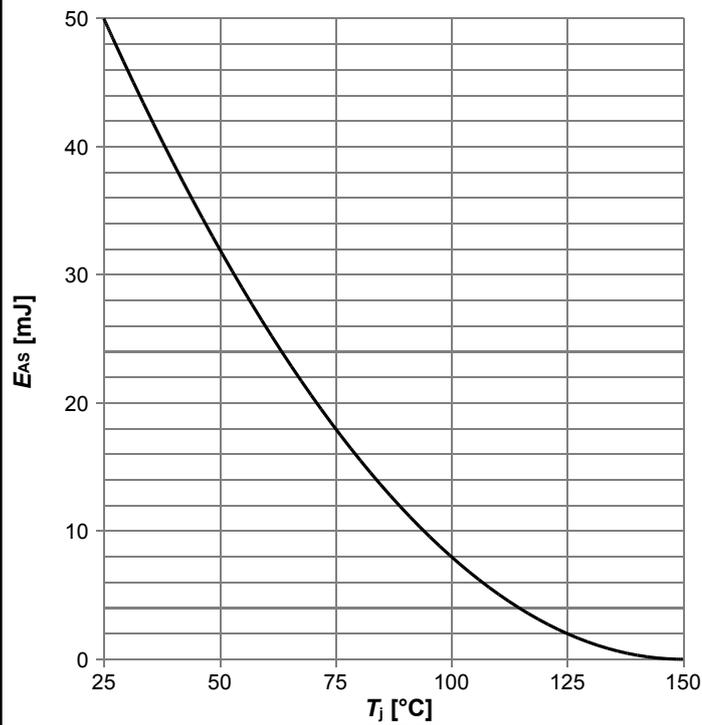
Diagram 12: Typ. output characteristics



$I_D=f(V_{DS})$; $T_j=25\text{ }^{\circ}\text{C}$; parameter: V_{GS}

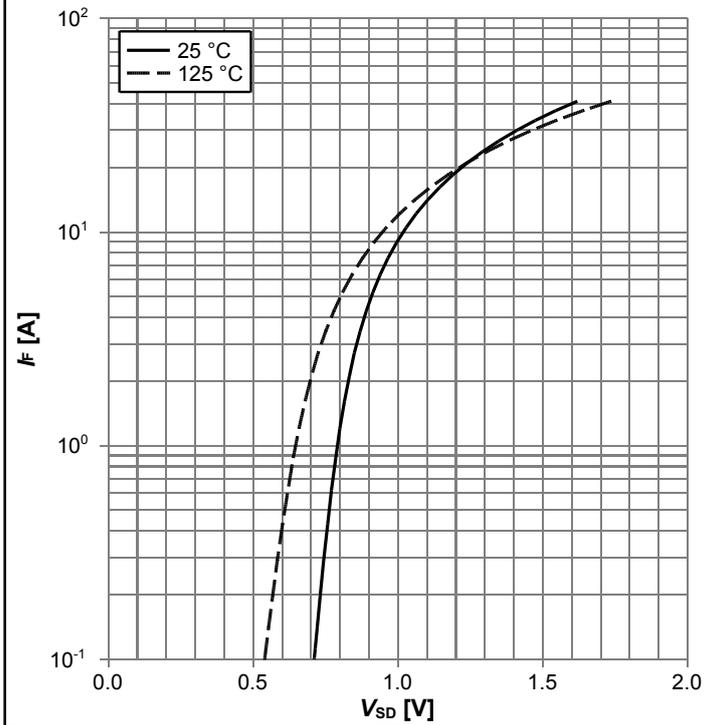
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Diagram 13: Avalanche energy



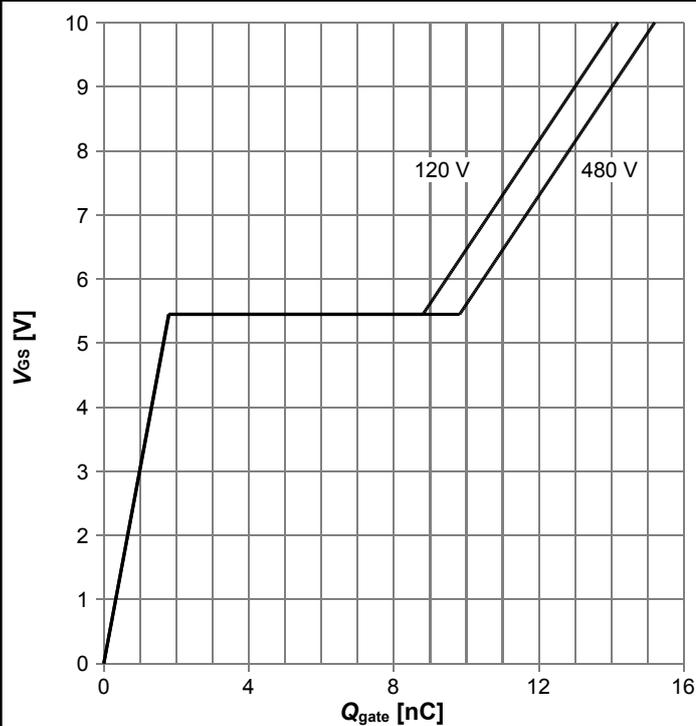
$E_{AS}=f(T_j)$; $I_D=1.0$ A; $V_{DD}=50$ V

Diagram 14: Forward characteristics of reverse diode



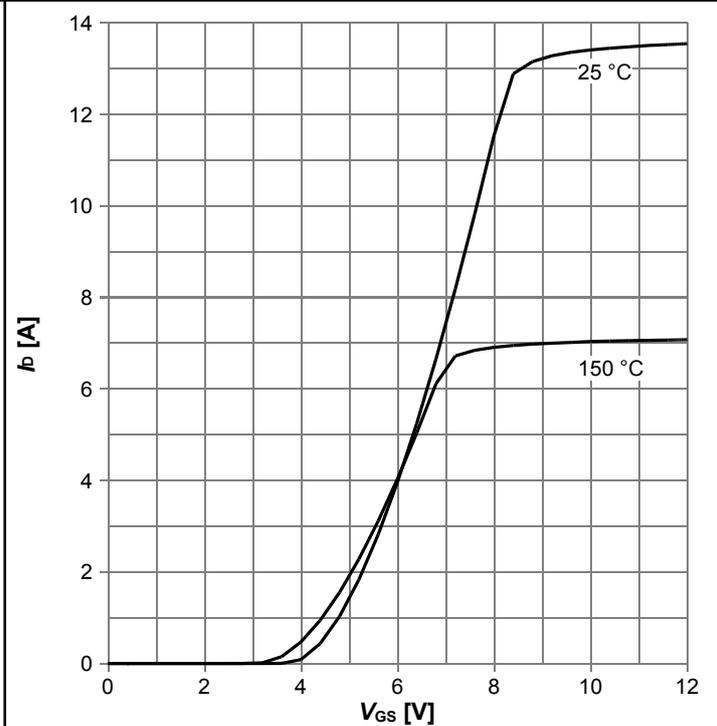
$I_F=f(V_{SD})$; parameter: T_j

Diagram 15: Typ. gate charge



$V_{GS}=f(Q_{gate})$; $I_D=2.2$ A pulsed; parameter: V_{DD}

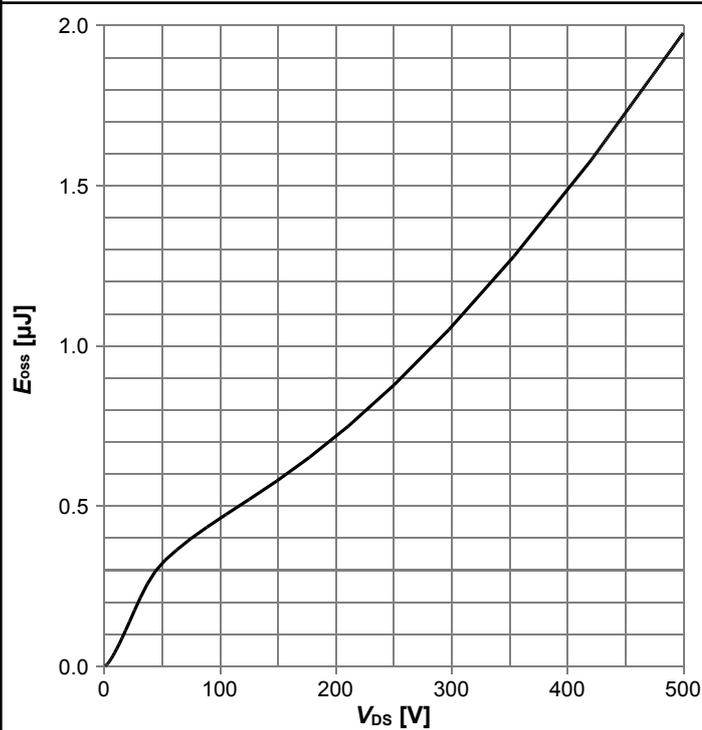
Diagram 16: Typ. transfer characteristics



$I_D=f(V_{GS})$; $V_{DS}=20$ V; parameter: T_j

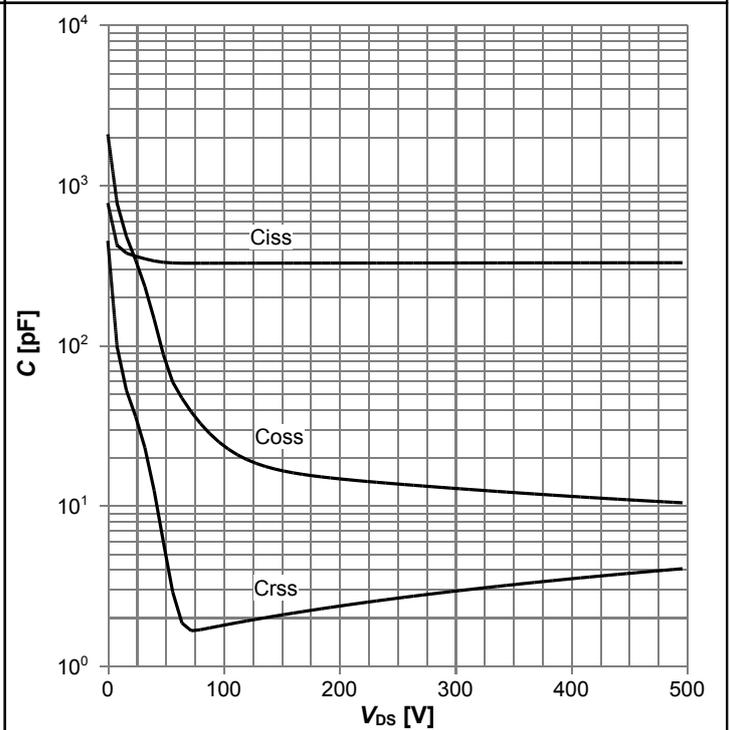
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Diagram 17: Typ. Coss stored energy



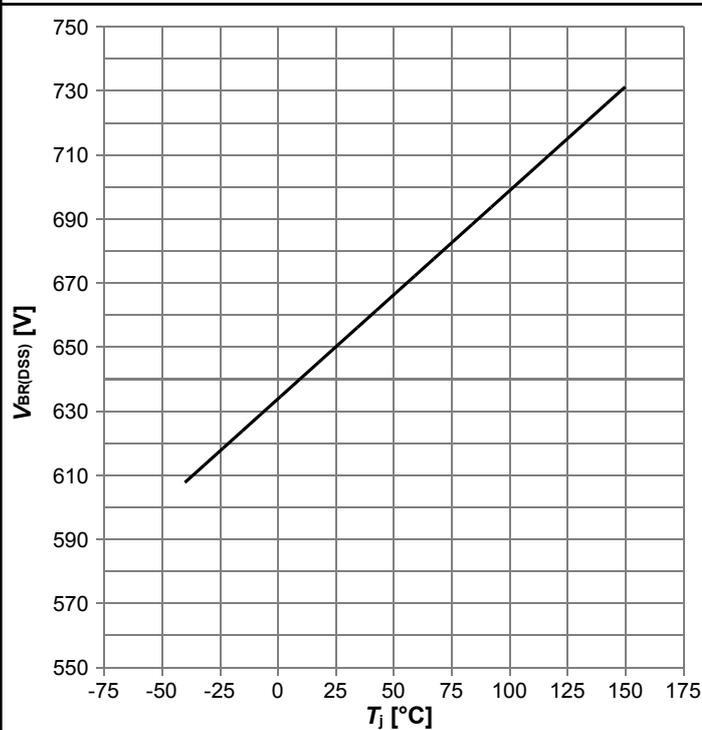
$E_{oss}=f(V_{DS})$

Diagram 18: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

Diagram 19: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j); I_D=1.0\text{ mA}$

5 Test Circuits

Table 8 Diode characteristics

Test circuit for diode characteristics	Diode recovery waveform

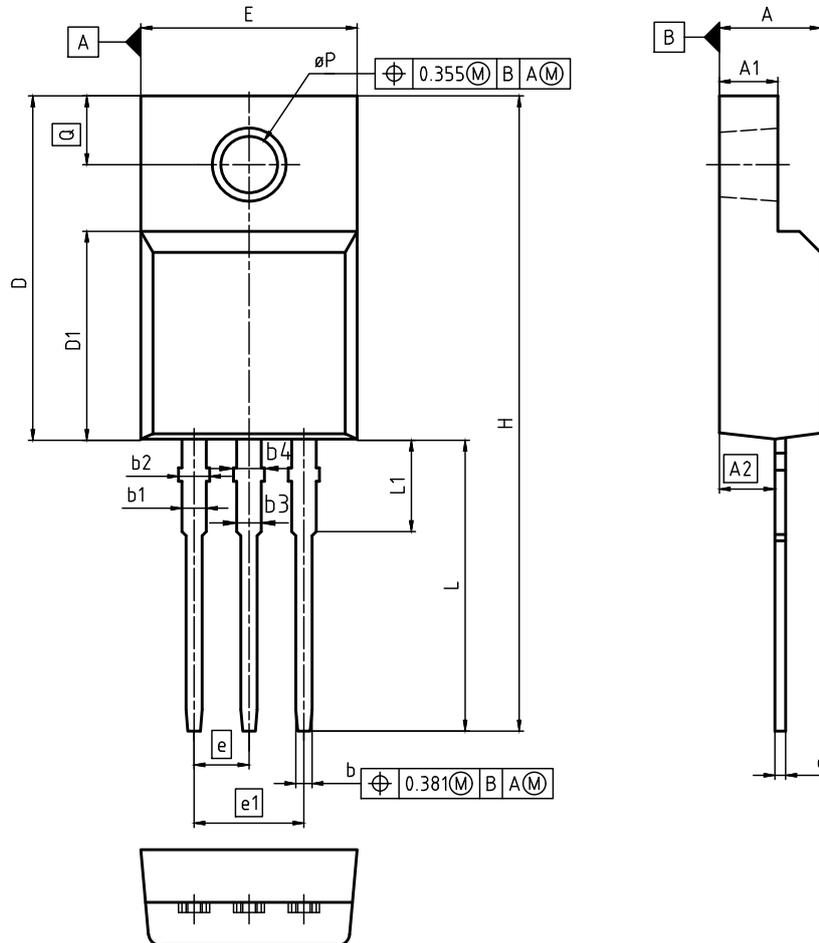
Table 9 Switching times

Switching times test circuit for inductive load	Switching times waveform

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

6 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.34	2.85	0.092	0.112
A2	2.42	2.86	0.095	0.113
b	0.65	0.90	0.026	0.035
b1	0.95	1.38	0.037	0.054
b2	0.95	1.51	0.037	0.059
b3	0.65	1.38	0.026	0.054
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.67	16.15	0.617	0.636
D1	8.97	9.83	0.353	0.387
E	10.00	10.65	0.394	0.419
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	3		3	
H	28.70	29.75	1.130	1.171
L	12.78	13.75	0.503	0.541
L1	2.83	3.45	0.111	0.136
$\varnothing P$	2.95	3.38	0.116	0.133
Q	3.15	3.50	0.124	0.138

Dimensions do not include mold flash, protrusions or gate burrs

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SCALE

EUROPEAN PROJECTION

ISSUE DATE
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REVISION
04

Figure 1 Outline PG-TO 220 FullPAK, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ CE Webpage: www.infineon.com
- IFX CoolMOS™ CE application note: www.infineon.com
- IFX CoolMOS™ CE simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPA65R1K0CE

Revision: 2016-02-19, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2016-02-19	Release of final version

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